

Document Title

64Kx8 bit Low Power CMOS Static RAM

Revision History

<u>Revision No.</u>	<u>History</u>	<u>Draft Data</u>	<u>Remark</u>
0.0	Initial draft	November 28, 1993	Design target
0.1	Revision	May 13, 1994	Preliminary
1.0	Finalize	December 1, 1994	Final
2.0	Revision - Add 45ns part with 30pf test load.	August 12, 1995	Final
3.0	Revision - Change Data Sheet format : One data sheets for industrial and commercial product	April 15, 1996	Final
4.0	Revision - Change Data Sheet format - Remove 45ns part from commercial product and 100ns part from industrial product - Remove low power part form TSOP package	January 9, 1998	Final

The attached data, sheets are provided by SAMSUNG Electronics. SAMSUNG Electronics CO., LTD. reserve the right to change the specifications and products. SAMSUNG Electronics will answer to your questions about device. If you have any questions, please contact the SAMSUNG branch offices.



64Kx8 bit Low Power CMOS Static RAM

FEATURES

- Process Technology: Poly Load
- Organization: 64Kx8
- Power Supply Voltage: 4.5~5.5V
- Low Data Retention Voltage: 2V(Min)
- Three state output and TTL Compatible
- Package Type: 32-SOP-525, 32-TSOP1-0820F

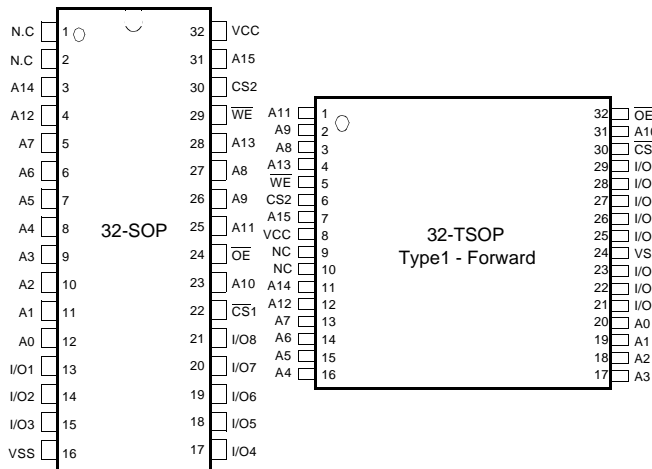
GENERAL DESCRIPTION

The KM68512A families are fabricated by SAMSUNG's advanced CMOS process technology. The families support various operating temperature ranges and have various package types for user flexibility of system design. The families also support low data retention voltage for battery back-up operation with low data retention current.

PRODUCT FAMILY

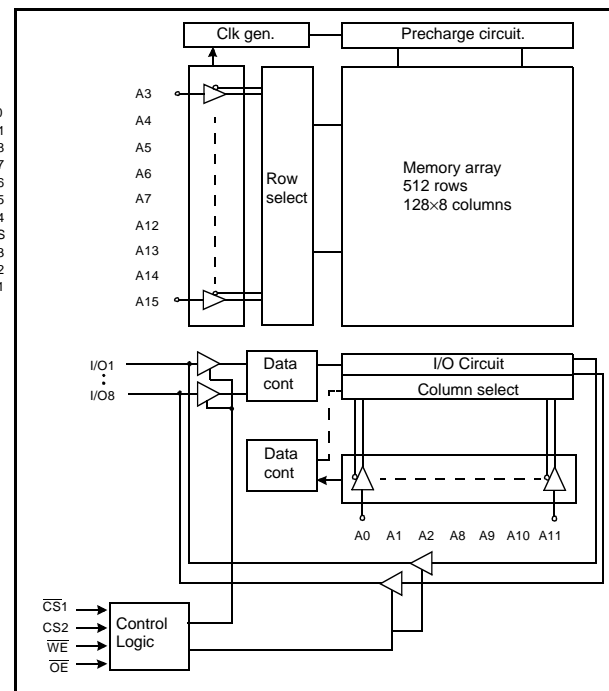
Product Family	Operating Temperature	Vcc Range	Speed	Power Dissipation		PKG Type
				Standby (I _{SB1} , Max)	Operating (I _{CC2} , Max)	
KM68512AL KM68512AL-L	Commercial (0~70°C)	4.5 to 5.5V	55/70ns	100µA 20µA	70mA	32-SOP 32-TSOP1-F
KM68512ALI KM68512ALI-L	Industrial (-40~85°C)		70ns	100µA 50µA		

PIN DESCRIPTION



Name	Function
$\overline{CS}_1, \overline{CS}_2$	Chip Select Inputs
\overline{OE}	Output Enable Input
\overline{WE}	Write Enable Input
A ₀ -A ₁₅	Address Inputs
I/O ₁ -I/O ₈	Data Inputs/Outputs
V _{cc}	Power
V _{ss}	Ground
N.C	No Connection

FUNCTIONAL BLOCK DIAGRAM



SAMSUNG ELECTRONICS CO., LTD. reserves the right to change products and specifications without notice.

PRODUCT LIST

Commercial Temperature Products(0~70°C)		Industrial Temperature Products(-40~85°C)	
Part Name	Function	Part Name	Function
KM68512ALG-5	32-SOP, 55ns, L-pwr	KM68512ALGI-7	32-SOP, 70ns, L-pwr
KM68512ALG-5L	32-SOP, 55ns, LL-pwr	KM68512ALGI-7L	32-SOP, 70ns, LL-pwr
KM68512ALG-7	32-SOP, 70ns, L-pwr		
KM68512ALG-7L	32-SOP, 70ns, LL-pwr	KM68512ALTI-7L	32-TSOP1-F, 70ns, LL-pwr
KM68512ALT-5L	32-TSOP1-F, 55ns, LL-pwr		
KM68512ALT-7L	32-TSOP1-F, 70ns, LL-pwr		

FUNCTIONAL DESCRIPTION

CS ₁	CS ₂	OE	WE	I/O Pin	Mode	Power
H	X ¹⁾	X ¹⁾	X ¹⁾	High-Z	Deselected	Standby
X ¹⁾	L	X ¹⁾	X ¹⁾	High-Z	Deselected	Standby
L	H	H	H	High-Z	Output Disabled	Active
L	H	L	H	Dout	Read	Active
L	H	X ¹⁾	L	Din	Write	Active

1. X means don't care.(Must be low or high state)

ABSOLUTE MAXIMUM RATINGS¹⁾

Item	Symbol	Ratings	Unit	Remark
Voltage on any pin relative to Vss	V _{IN} ,V _{OUT}	-0.5 to 7.0	V	-
Voltage on Vcc supply relative to Vss	V _{CC}	-0.5 to 7.0	V	-
Power Dissipation	P _D	1.0	W	-
Storage temperature	T _{STG}	-65 to 150	°C	-
Operating Temperature	T _A	0 to 70	°C	KM68512A
		-40 to 85	°C	KM68512AI
Soldering temperature and time	T _{SOLDER}	260°C, 10sec(Lead Only)	-	-

1. Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. Functional operation should be restricted to recommended operating condition. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

RECOMMENDED DC OPERATING CONDITIONS¹⁾

Item	Symbol	Min	Typ	Max	Unit
Supply voltage	V _{CC}	4.5	5.0	5.5	V
Ground	V _{SS}	0	0	0	V
Input high voltage	V _{IH}	2.2	-	V _{CC} +0.5V ²⁾	V
Input low voltage	V _{IL}	-0.5 ³⁾	-	0.8	V

Note

- Commercial Product : T_A=0 to 70°C, unless otherwise specified
Industrial Product : T_A=-40 to 85°C, unless otherwise specified
- Overshoot : V_{CC}+3.0V in case of pulse width≤30ns
- Undershoot : -3.0V in case of pulse width≤30ns
- Overshoot and undershoot are sampled, not 100% tested

CAPACITANCE¹⁾(f=1MHz, T_A=25°C)

Item	Symbol	Test Condition	Min	Max	Unit
Input capacitance	C _{IN}	V _{IN} =0V	-	6	pF
Input/Output capacitance	C _{IO}	V _{IO} =0V	-	8	pF

- Capacitance is sampled, not 100% tested

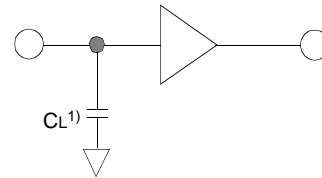
DC AND OPERATING CHARACTERISTICS

Item	Symbol	Test Conditions	Min	Typ	Max	Unit	
Input leakage current	I _{LI}	V _{IN} =V _{SS} to V _{CC}	-1	-	1	μA	
Output leakage current	I _{LO}	$\overline{CS}_1=V_{IH}$ or $CS_2=V_{IL}$ or $\overline{OE}=V_{IH}$ or $\overline{WE}=V_{IL}$, V _{IO} =V _{SS} to V _{CC}	-1	-	1	μA	
Operating power supply current	I _{CC}	I _{IO} =0mA, $\overline{CS}_1=V_{IL}$, CS ₂ =V _{IH} , V _{IN} =V _{IH} or V _{IL}	-	7	15	mA	
Average operating current	I _{CC1}	Cycle time=1μs, 100% duty, I _{IO} =0mA CS ₁ ≤0.2V, CS ₂ ≥V _{CC} -0.2V, V _{IN} ≤0.2V or V _{IN} ≥V _{CC} -0.2V	-	-	10	mA	
	I _{CC2}	Cycle time=Min, 100% duty, I _{IO} =0mA, $\overline{CS}_1=V_{IL}$, CS ₂ =V _{IH} , V _{IN} =V _{IH} or V _{IL}	-	-	70	mA	
Output low voltage	V _{OL}	I _{OL} =2.1mA	-	-	0.4	V	
Output high voltage	V _{OH}	I _{OH} =-1.0mA	2.4	-	-	V	
Standby Current(TTL)	I _{SB}	$\overline{CS}_1=V_{IH}$, CS ₂ =V _{IL} , Other inputs =V _{IH} or V _{IL}	-	-	3	mA	
Standby Current (CMOS)	KM68512AL/L-L	I _{SB1} $\overline{CS}_1 \geq V_{CC}-0.2V$, CS ₂ ≥V _{CC} -0.2V or CS ₂ ≤0.2V Other inputs =0 - V _{CC}	Low Power	-	2	100	μA
			Low Low Power	-	1	20	
	KM68512ALI/LI-L		Low Power	-	2	100	μA
			Low Low Power	-	1	50	

AC OPERATING CONDITIONS

TEST CONDITIONS (Test Load and Input/Output Reference)

Input pulse level : 0.8 to 2.4V
 Input rising and falling time : 5ns
 Input and output reference voltage : 1.5V
 Output load(see right) : $CL=100pF+1TTL$



1. Including scope and jig capacitance

AC CHARACTERISTICS ($V_{CC}=4.5\sim 5.5V$, KM68512A Family: $T_A=0$ to $70^\circ C$, KM68512AI Family: $T_A=-40$ to $85^\circ C$)

Parameter List		Symbol	Speed Bins				Units
			55ns		70ns		
			Min	Max	Min	Max	
Read	Read cycle time	t _{RC}	55	-	70	-	ns
	Address access time	t _{AA}	-	55	-	70	ns
	Chip select to output	t _{CO1} , t _{CO2}	-	55	-	70	ns
	Output enable to valid output	t _{OE}	-	25	-	35	ns
	Chip select to low-Z output	t _{LZ}	10	-	10	-	ns
	Output enable to low-Z output	t _{OLZ}	5	-	5	-	ns
	Chip disable to high-Z output	t _{HZ}	0	20	0	25	ns
	Output disable to high-Z output	t _{OHZ}	0	20	0	25	ns
	Output hold from address change	t _{OH}	10	-	10	-	ns
Write	Write cycle time	t _{WC}	55	-	70	-	ns
	Chip select to end of write	t _{CW}	45	-	60	-	ns
	Address set-up time	t _{AS}	0	-	0	-	ns
	Address valid to end of write	t _{AW}	45	-	60	-	ns
	Write pulse width	t _{WP}	40	-	50	-	ns
	Write recovery time	t _{WR}	0	-	0	-	ns
	Write to output high-Z	t _{WHZ}	0	20	0	25	ns
	Data to write time overlap	t _{DW}	25	-	30	-	ns
	Data hold from write time	t _{DH}	0	-	0	-	ns
	End write to output low-Z	t _{OW}	5	-	5	-	ns

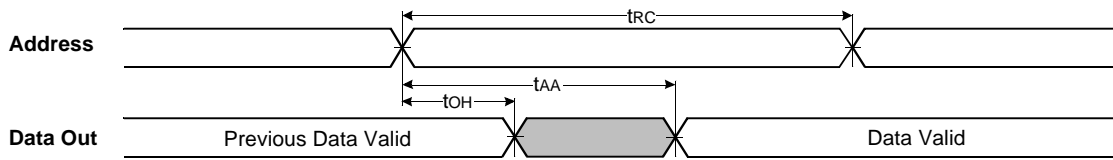
DATA RETENTION CHARACTERISTICS

Item	Symbol	Test Condition	Min	Typ	Max	Unit	
V _{CC} for data retention	V _{DR}	$\overline{CS}_1 \geq V_{CC}-0.2V$	2.0	-	5.5	V	
Data retention current	I _{DR}	$V_{CC}=3.0V$ $\overline{CS}_1 \geq V_{CC}-0.2V$ $CS_2 \geq V_{CC}-0.2V$ or $CS_2 \leq 0.2V$	L-Ver	-	1	50	μA
			LL-Ver	-	0.5	10	
			L-Ver	-	-	50	
			LL-Ver	-	-	25	
Data retention set-up time	t _{SDR}	See data retention waveform	0	-	-	ms	
Recovery time	t _{RDR}		5	-	-		

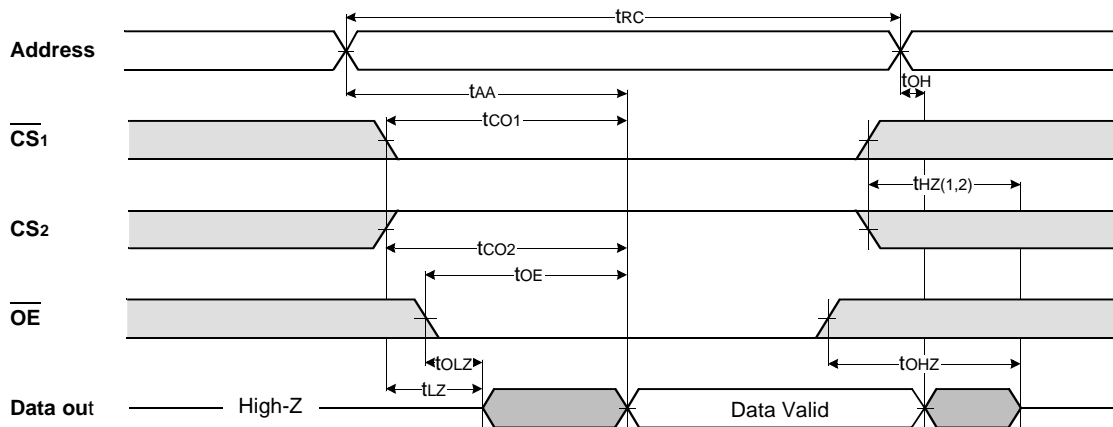
1. $\overline{CS}_1 \geq V_{CC}-0.2V$, $CS_2 \geq V_{CC}-0.2V$ (\overline{CS}_1 controlled) or $CS_2 \leq 0.2V$ (CS_2 controlled).

TIMMING DIAGRAMS

TIMING WAVEFORM OF READ CYCLE(1) (Address Controlled, $\overline{CS1}=\overline{OE}=V_{IL}$, $\overline{WE}=V_{IH}$)



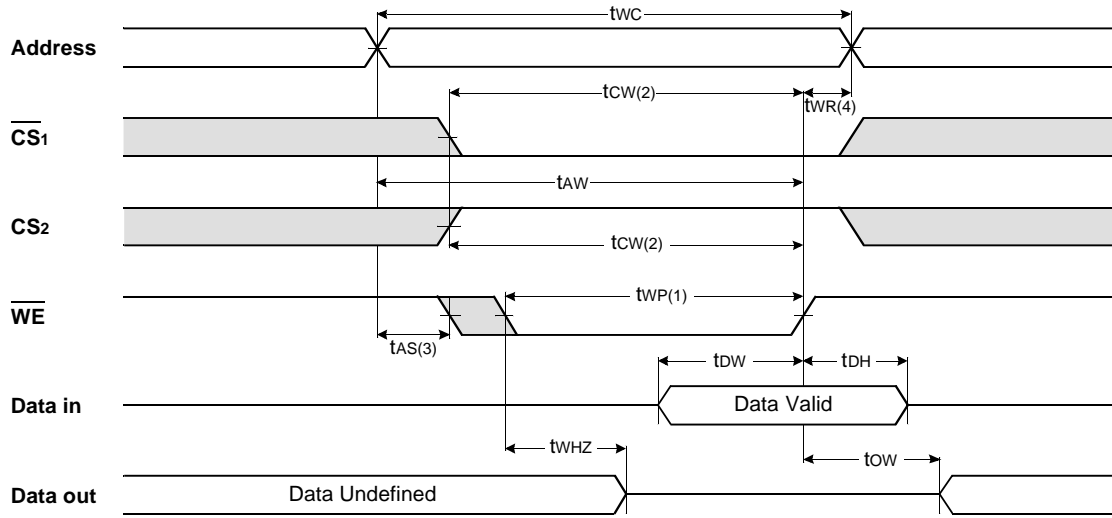
TIMING WAVEFORM OF READ CYCLE(2) ($\overline{WE}=V_{IH}$)



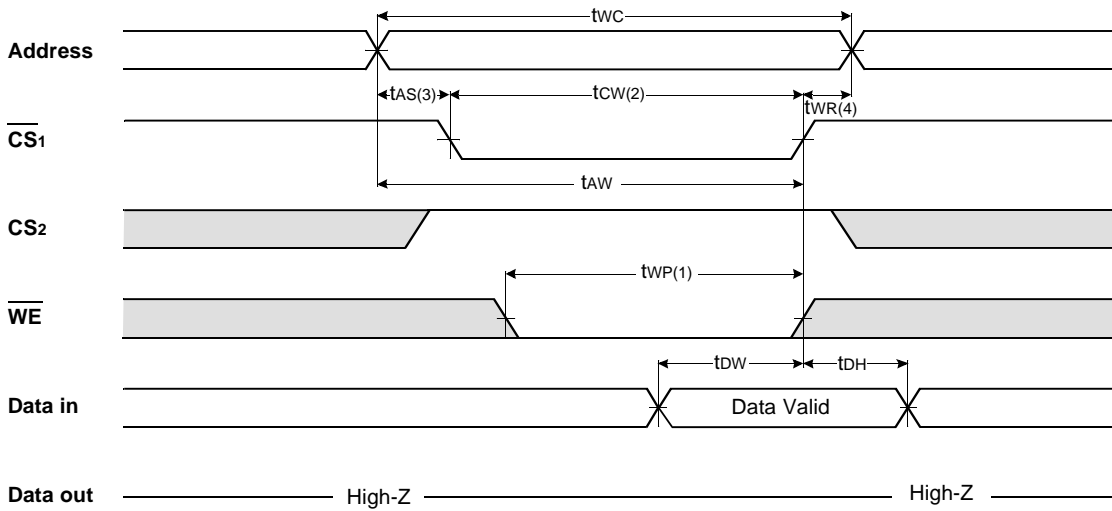
NOTES (READ CYCLE)

1. t_{HZ} and t_{OHZ} are defined as the time at which the outputs achieve the open circuit conditions and are not referenced to output voltage levels.
2. At any given temperature and voltage condition, $t_{HZ}(\text{Max.})$ is less than $t_{LZ}(\text{Min.})$ both for a given device and from device to device interconnection.

TIMING WAVEFORM OF WRITE CYCLE(1) (\overline{WE} Controlled)

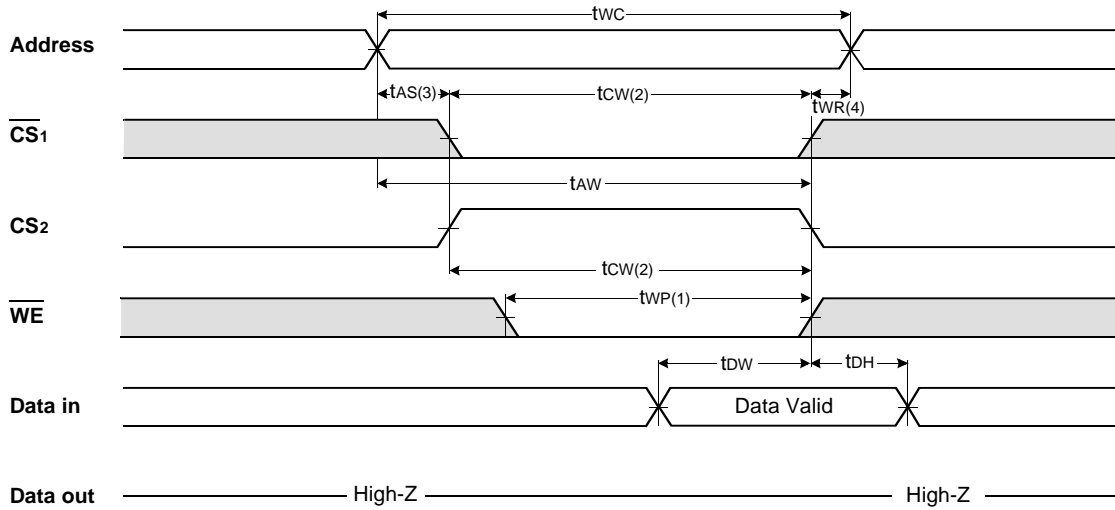


TIMING WAVEFORM OF WRITE CYCLE(2) ($\overline{CS1}$ Controlled)



Downloaded from Elcodis.com electronic components distributor

TIMING WAVEFORM OF WRITE CYCLE(3) (CS₂ Controlled)

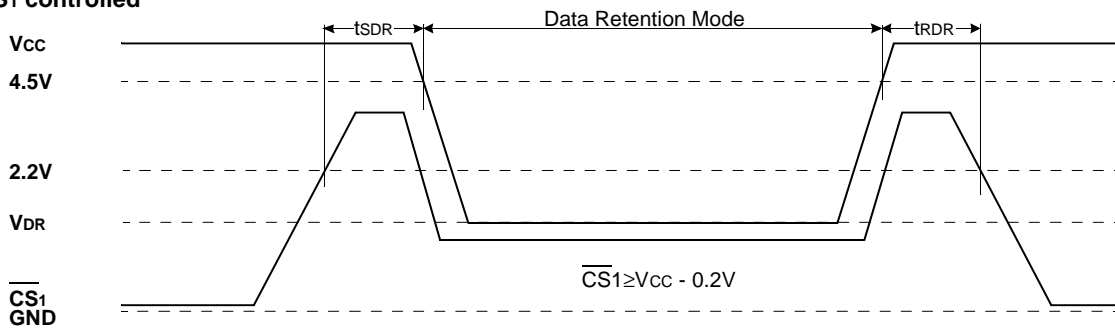


NOTES (WRITE CYCLE)

1. A write occurs during the overlap of a low \overline{CS}_1 , a high \overline{CS}_2 and a low \overline{WE} . A write begins at the latest transition among \overline{CS}_1 going low, \overline{CS}_2 going high and \overline{WE} going low : A write ends at the earliest transition among \overline{CS}_1 going high, \overline{CS}_2 going low and \overline{WE} going high, t_{WP} is measured from the beginning of write to the end of write.
2. t_{CW} is measured from the \overline{CS}_1 going low or \overline{CS}_2 going high to the end of write.
3. t_{AS} is measured from the address valid to the beginning of write.
4. t_{WR} is measured from the end of write to the address change. $t_{WR(1)}$ applied in case a write ends as \overline{CS}_1 or \overline{WE} going high $t_{WR(2)}$ applied in case a write ends as \overline{CS}_2 going to low.

DATA RETENTION WAVE FORM

\overline{CS}_1 controlled



CS₂ controlled

